

Schottky Power Rectifier

Surface Mount Power Package

MBRS130LT3G, SBR8130LT3G, SBR8130LN

This device employs the Schottky Barrier principle in a large area metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for low voltage, high frequency rectification, or as free wheeling and polarity protection diodes, in surface mount applications where compact size and weight are critical to the system.

Features

- Very Low Forward Voltage Drop (0.395 Volts Max @ 1.0 A, $T_J = 25^\circ\text{C}$)
- Small Compact Surface Mountable Package with J-Bend Leads
- Highly Stable Oxide Passivated Junction
- Guard-Ring for Stress Protection
- ESD Ratings:
 - ♦ Human Body Model = 3B (> 16000 V)
 - ♦ Machine Model = C (> 400 V)
- SBR8 Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable*
- These are Pb-Free Devices

Mechanical Characteristics

- Case: Epoxy, Molded
- Weight: 100 mg (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Cathode Polarity Band



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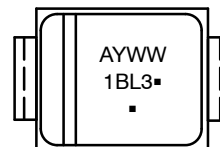
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SCHOTTKY BARRIER RECTIFIER 1.0 AMPERE 30 VOLTS



SMB
CASE 403A

MARKING DIAGRAM



1BL3 = Specific Device Code
A = Assembly Location**
Y = Year
WW = Work Week
▪ = Pb-Free Package

(Note: Microdot may be in either location)

**The Assembly Location code (A) is front side optional. In cases where the Assembly Location is stamped in the package bottom (molding ejecter pin), the front side assembly code may be blank.

ORDERING INFORMATION

Device	Package	Shipping†
MBRS130LT3G	SMB (Pb-Free)	2,500 / Tape & Reel
SBR8130LT3G*	SMB (Pb-Free)	2,500 / Tape & Reel
SBR8130LT3G-VF01*	SMB (Pb-Free)	2,500 / Tape & Reel
SBR8130LNT3G*	SMB (Pb-Free)	2,500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	30	V
Average Rectified Forward Current $T_L = 120^\circ\text{C}$ $T_L = 110^\circ\text{C}$	$I_{F(AV)}$	1.0 2.0	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I_{FSM}	40	A
Operating Junction Temperature	T_J	-65 to +125	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Lead	Ψ_{JL}	12	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient ($T_A = 25^\circ\text{C}$, Min Pad, 1 oz copper) Junction-to-Ambient ($T_A = 25^\circ\text{C}$, 1" Pad, 1 oz copper)	$R_{\theta JA}$	228.8 71.3	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 1) ($I_F = 1.0\text{ A}$, $T_J = 25^\circ\text{C}$) ($I_F = 2.0\text{ A}$, $T_J = 25^\circ\text{C}$)	V_F	0.395 0.445	V
Maximum Instantaneous Reverse Current (Note 1) (Rated dc Voltage, $T_J = 25^\circ\text{C}$) (Rated dc Voltage, $T_J = 100^\circ\text{C}$)	I_R	1.0 10	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2\%$.

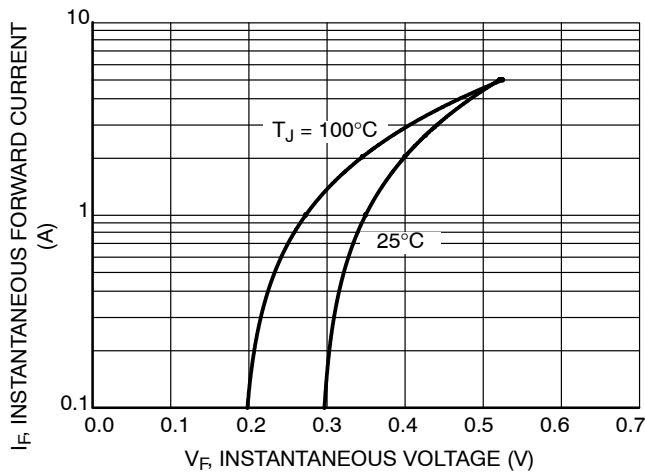


Figure 1. Typical Forward Voltage

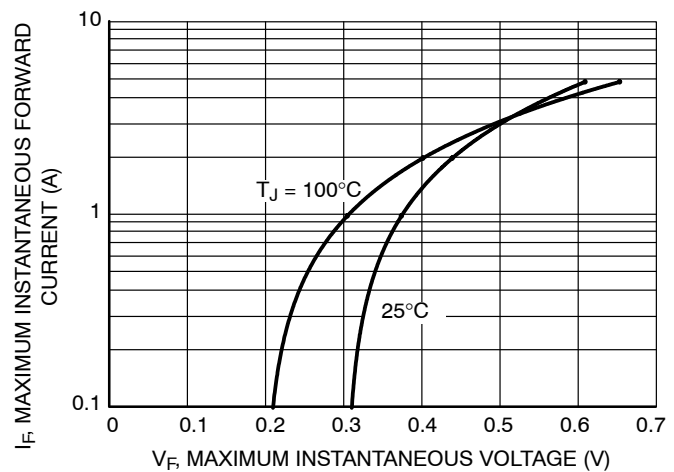


Figure 2. Maximum Forward Voltage

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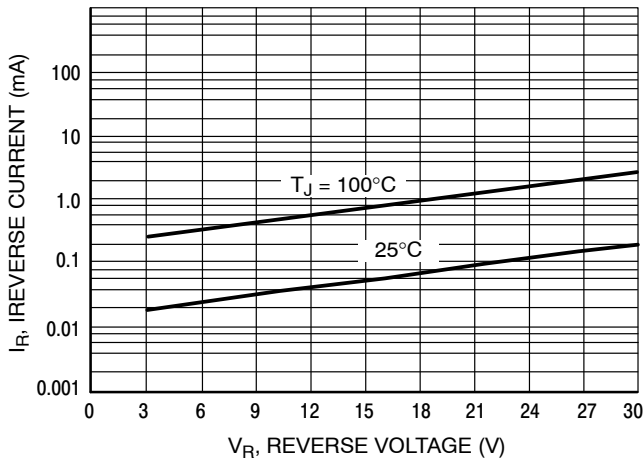


Figure 3. Typical Reverse Leakage Current

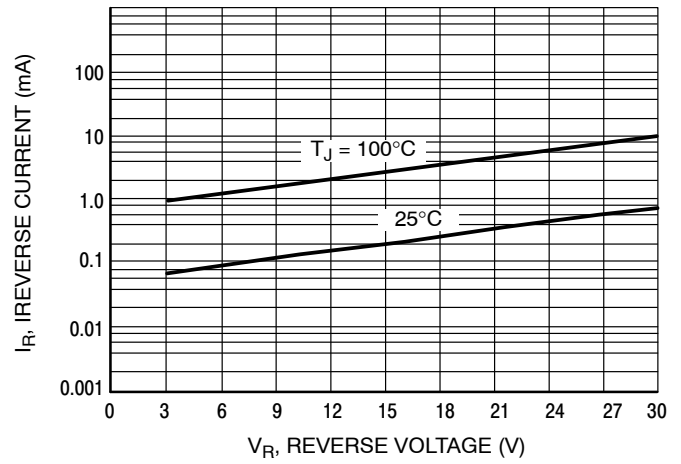


Figure 4. Typical Maximum Reverse Leakage Current

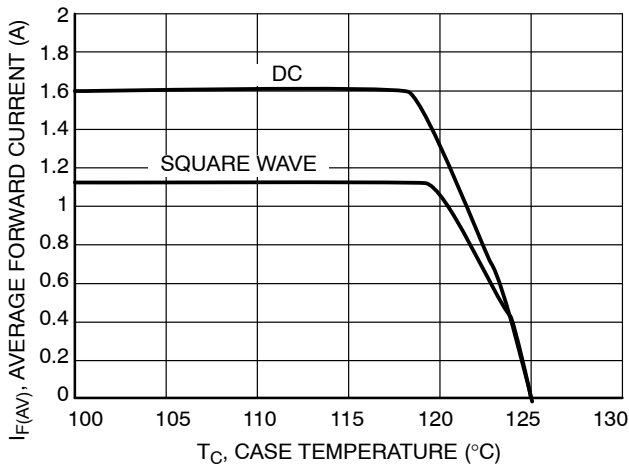


Figure 5. Current Derating (Case)

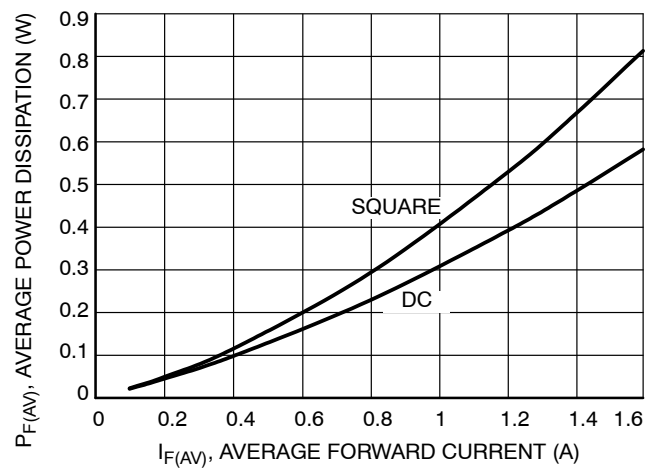


Figure 6. Typical Power Dissipation

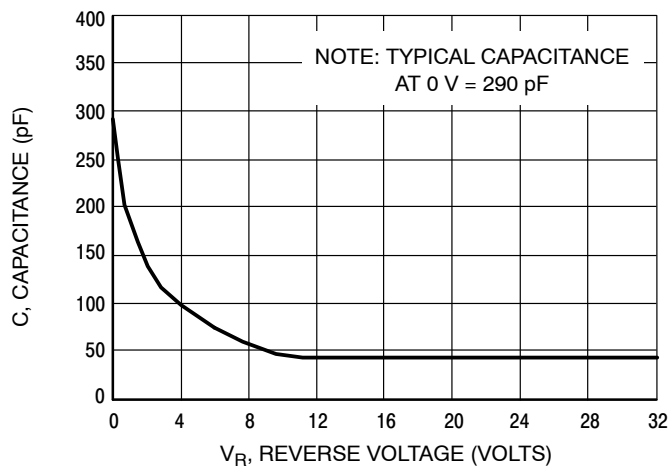


Figure 7. Typical Capacitance

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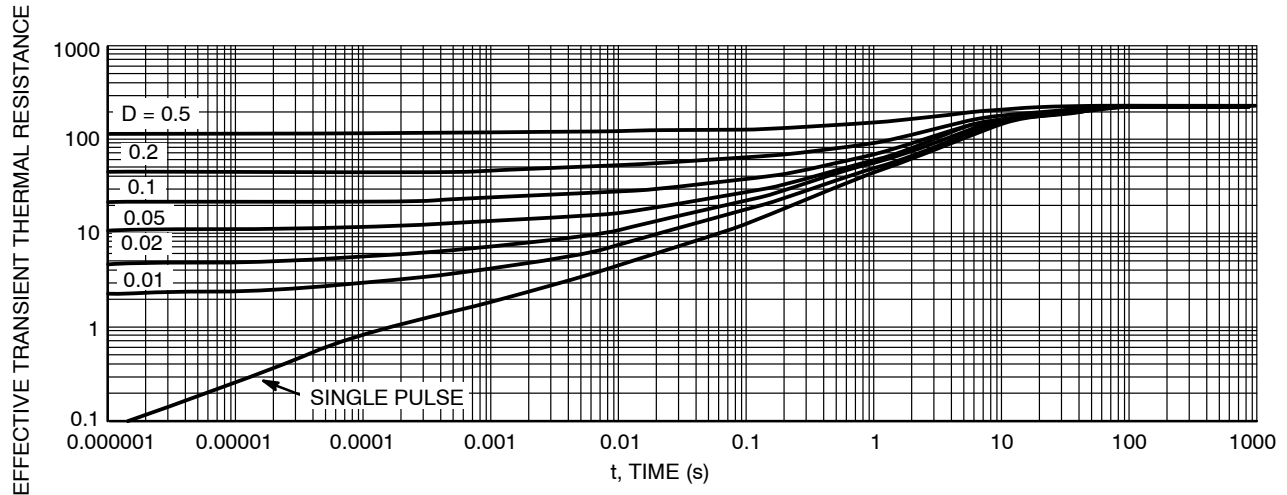


Figure 8. Thermal Response, Min Pad

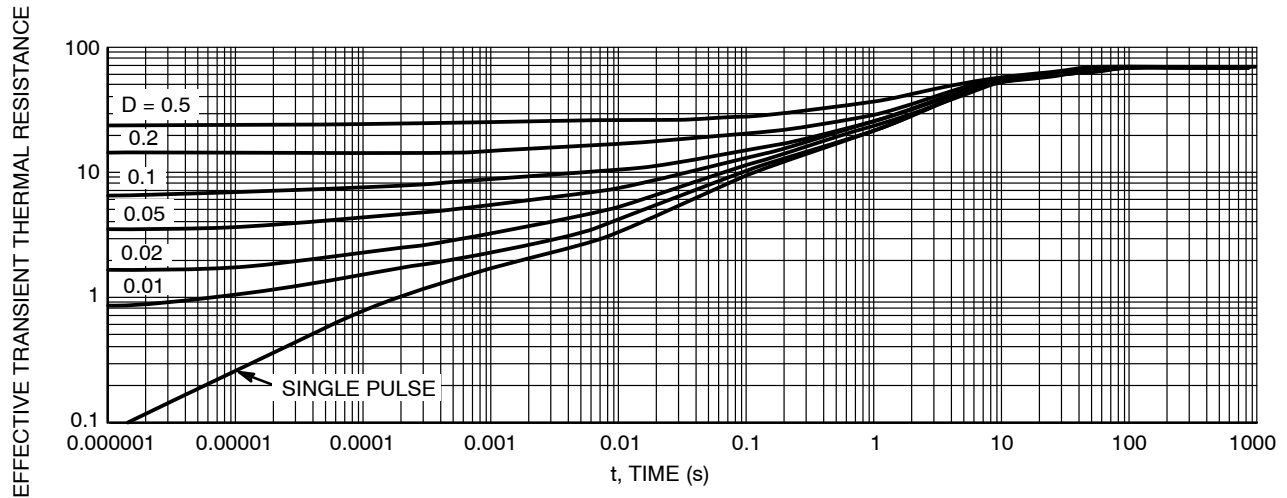


Figure 9. Thermal Response, 1 Inch Pad

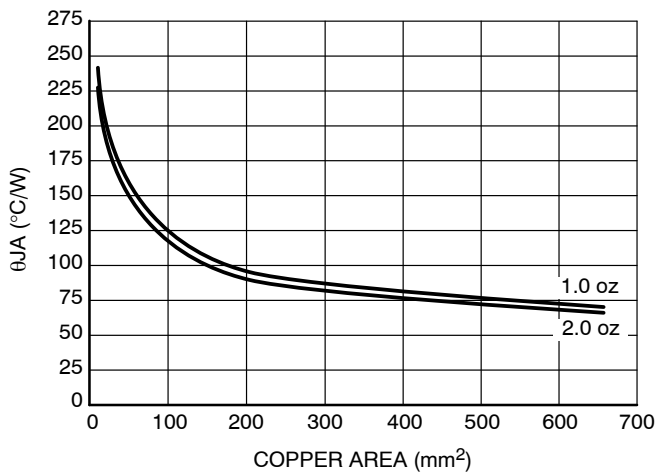


Figure 10. Thermal Resistance vs. Copper Area

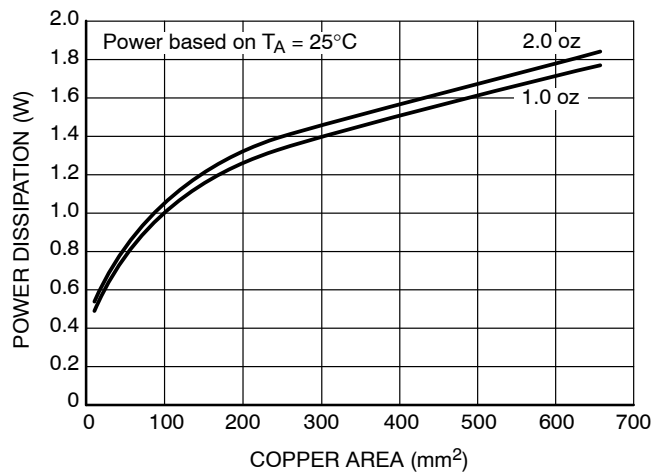


Figure 11. Power Dissipation vs. Copper Area

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

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SCALE 1:1

Polarity Band

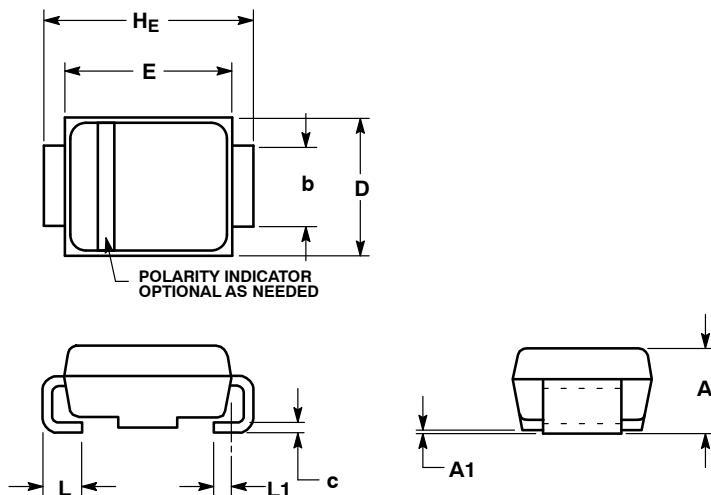


SCALE 1:1

Non-Polarity Band

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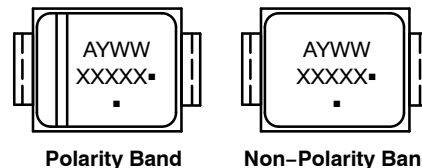


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION b SHALL BE MEASURED WITHIN DIMENSION L1.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.95	2.30	2.47	0.077	0.091	0.097
A1	0.05	0.10	0.20	0.002	0.004	0.008
b	1.96	2.03	2.20	0.077	0.080	0.087
c	0.15	0.23	0.31	0.006	0.009	0.012
D	3.30	3.56	3.95	0.130	0.140	0.156
E	4.06	4.32	4.60	0.160	0.170	0.181
HE	5.21	5.44	5.60	0.205	0.214	0.220
L	0.76	1.02	1.60	0.030	0.040	0.063
L1	0.51 REF			0.020 REF		

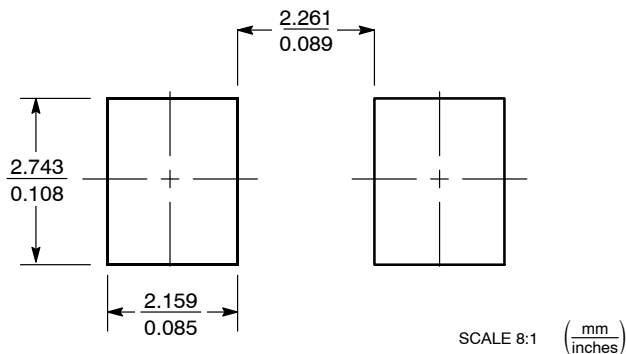
GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code
 A = Assembly Location
 Y = Year
 WW = Work Week
 ■ = Pb-Free Package
 (Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present.

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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